



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

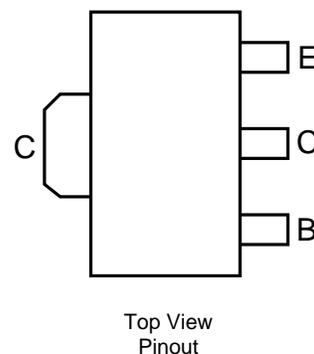
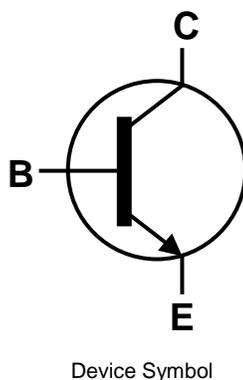
- $BV_{CE0} > 60V$
- $I_C = 3A$ High Continuous Collector Current
- I_{CM} up to 6A Peak Pulse Current
- 2W Power Dissipation
- Low Saturation Voltage $V_{CE(sat)} < 300mV @ 1A$
- Complementary PNP Type: DIODES™ NK-DXT751

Mechanical Data

- Package: SOT89
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.052 grams (Approximate)
Max Soldering Temperature +260°C for 30 secs as per JEDEC J-STD-020

Applications

- Load management functions
- Motor controls
- DC-DC / DC-AC converters



Maximum Ratings (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

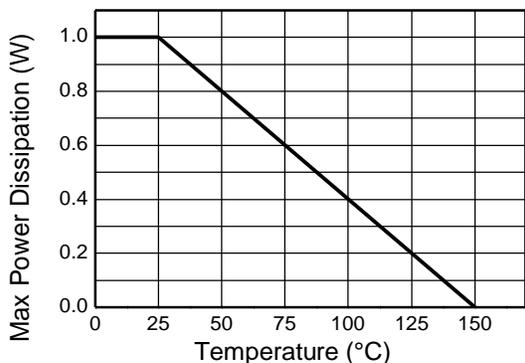
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	80	V
Collector-Emitter Voltage	V_{CE0}	60	V
Emitter-Base Voltage	V_{EB0}	5	V
Collector Current	I_C	3	A
Peak Pulse Collector Current	I_{CM}	6	A
Base Current	I_B	500	mA

Thermal Characteristics (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

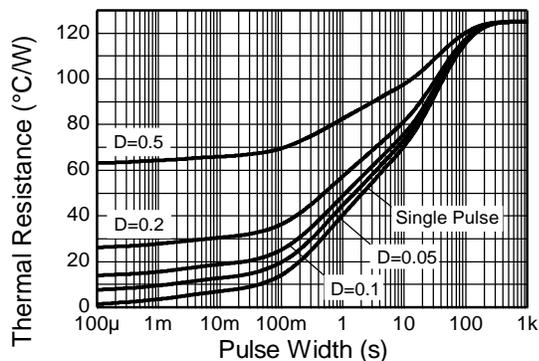
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	1	W
		2	
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	125	$^{\circ}\text{C/W}$
		62.5	
Thermal Resistance, Junction to Case	$R_{\theta JC}$	26	$^{\circ}\text{C/W}$
Thermal Resistance, Junction to Leads	$R_{\theta JL}$	6	$^{\circ}\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^{\circ}\text{C}$

- Notes:
5. For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in steady state condition.
 6. Same as note (5), except the device is mounted on 40mm x 40mm x 1.6mm FR4 PCB.
 7. Thermal resistance from junction to solder-point (on the exposed collector pad).

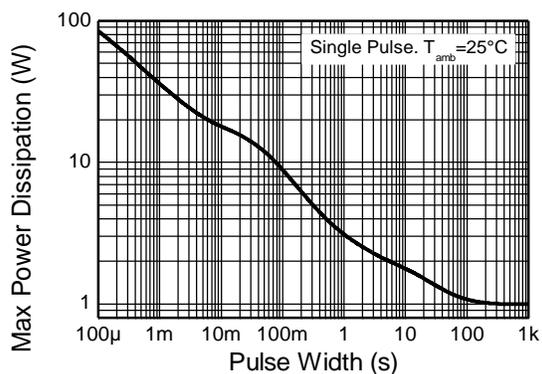
Thermal Characteristics and Derating Information



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	80	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 8)	BV_{CEO}	60	—	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	$I_E = 100\mu\text{A}$
Collector-Base Cutoff Current	I_{CBO}	—	—	0.1 10	μA	$V_{CB} = 60\text{V}$ $V_{CB} = 60\text{V}, T_A = +100^\circ\text{C}$
Emitter-Base Cutoff Current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 4\text{V}$
ON CHARACTERISTICS (Note 8)						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	0.08 0.23	0.3 0.6	V	$I_C = 1\text{A}, I_B = 100\text{mA}$ $I_C = 3\text{A}, I_B = 300\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	0.85	1.25	V	$I_C = 1\text{A}, I_B = 100\text{mA}$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	—	0.8	1	V	$V_{CE} = 2\text{V}, I_C = 1\text{A}$
DC Current Gain	h_{FE}	70 100 80 40	200 200 185 120	— 300 — —	—	$V_{CE} = 2\text{V}, I_C = 50\text{mA}$ $V_{CE} = 2\text{V}, I_C = 500\text{mA}$ $V_{CE} = 2\text{V}, I_C = 1\text{A}$ $V_{CE} = 2\text{V}, I_C = 2\text{A}$
SMALL-SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	140	200	—	MHz	$V_{CE} = 5\text{V}, I_C = 100\text{mA}, f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	—	30	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Switching Times	t_{on} t_{off}	— —	35 230	— —	ns ns	$V_{CC} = 10\text{V}, I_C = 500\text{mA}, I_{B1} = -I_{B2} = 50\text{mA}$

 Note: 8. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

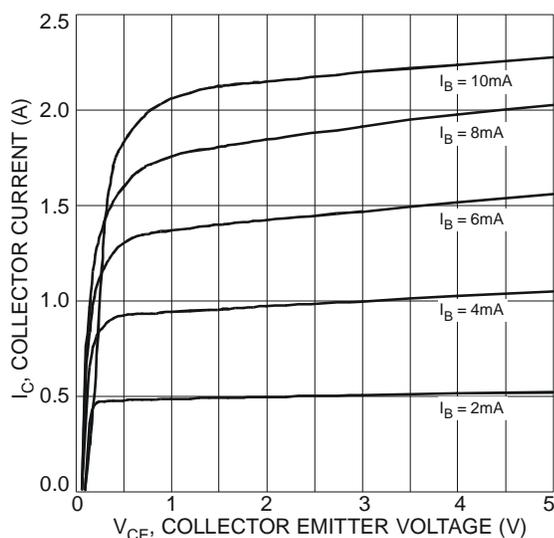
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)


Figure 1 Typical Collector Current vs. Collector-Emitter Voltage

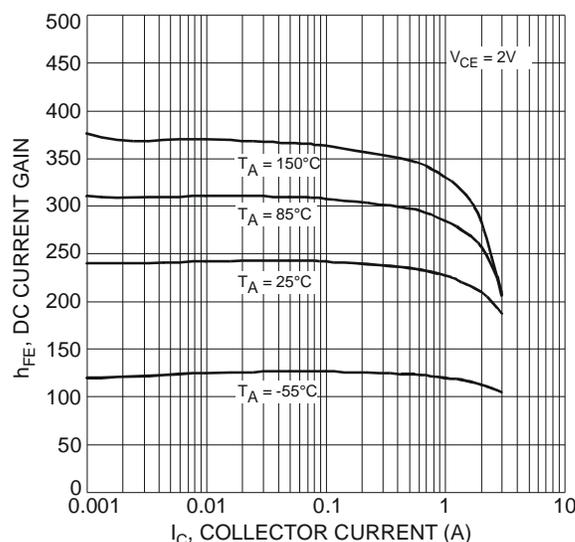


Figure 2 Typical DC Current Gain vs. Collector Current

Typical Electrical Characteristics (Continued)

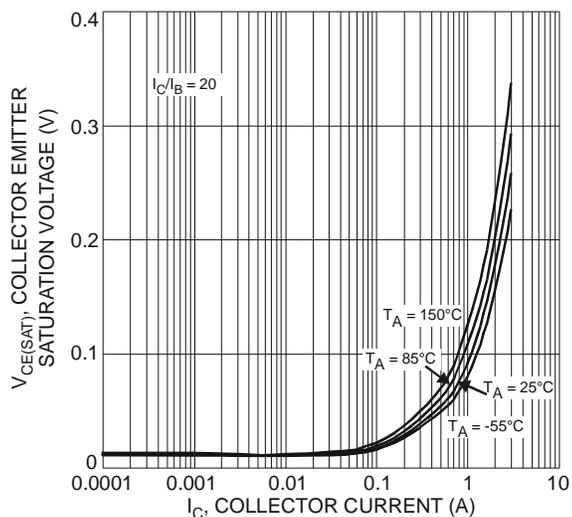


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

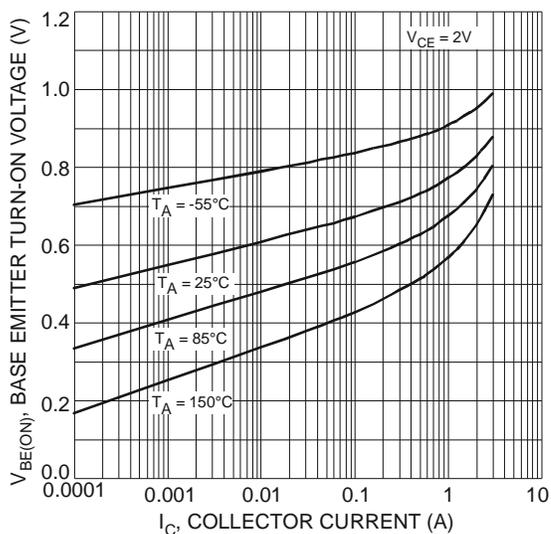


Figure 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

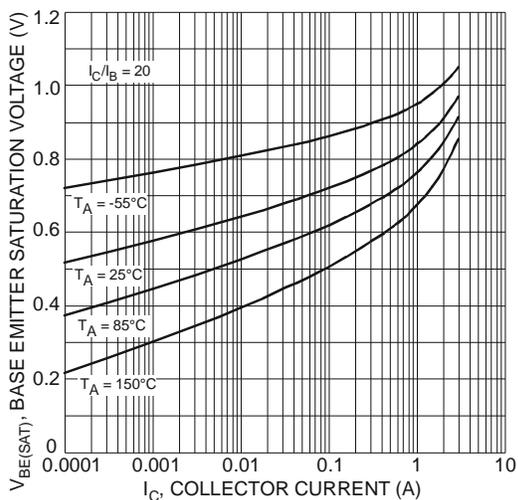


Figure 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

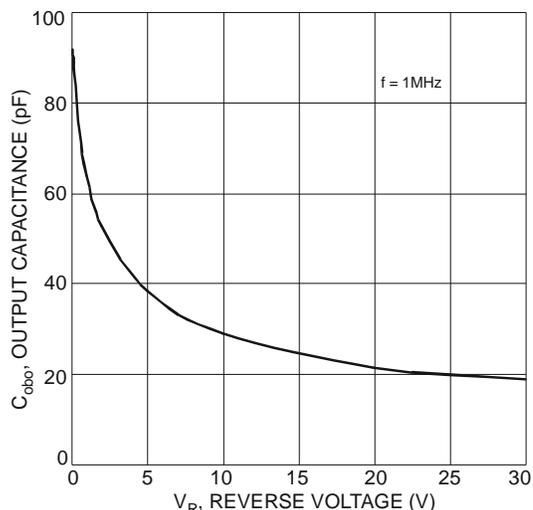


Figure 6 Typical Output Capacitance Characteristics

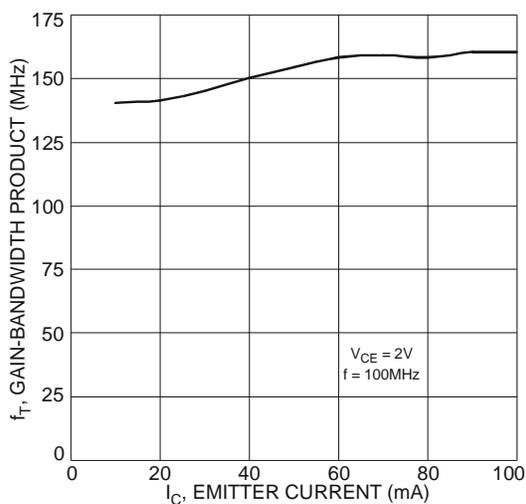
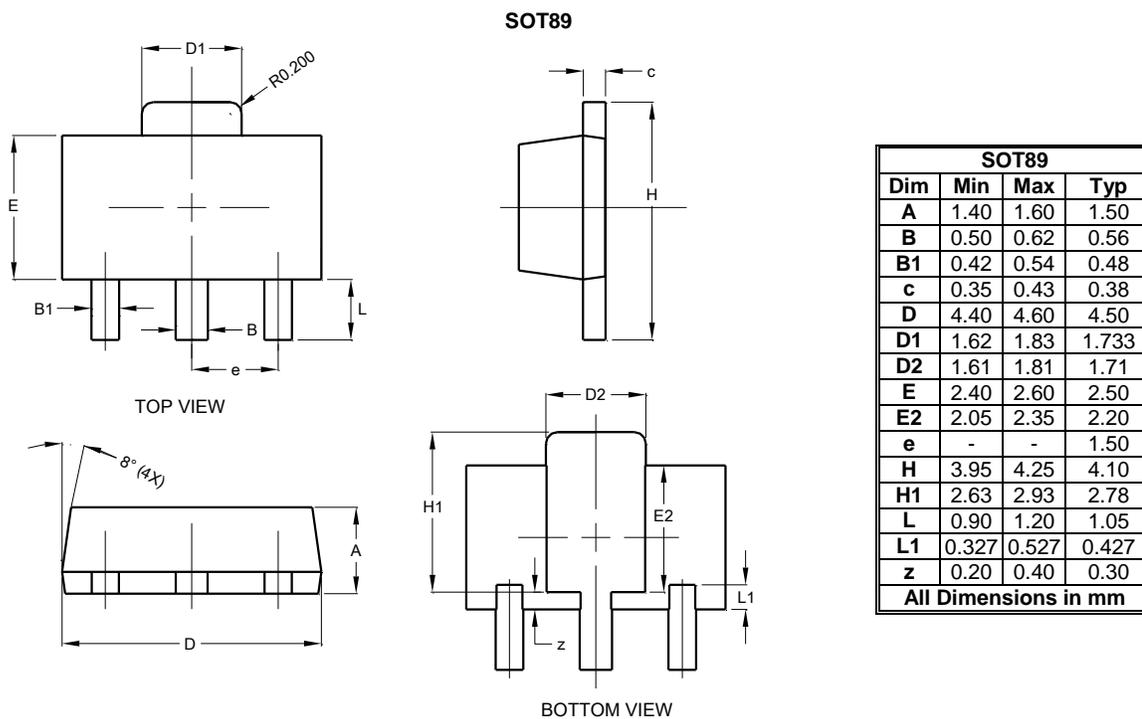


Figure 7 Typical Gain-Bandwidth Product vs. Emitter Current

Package Outline Dimensions



Suggested Pad Layout

